



Microelectronics for next generation of HEP instrumentation

Farah Fahim

Engineering retreat

24 Feb 2021

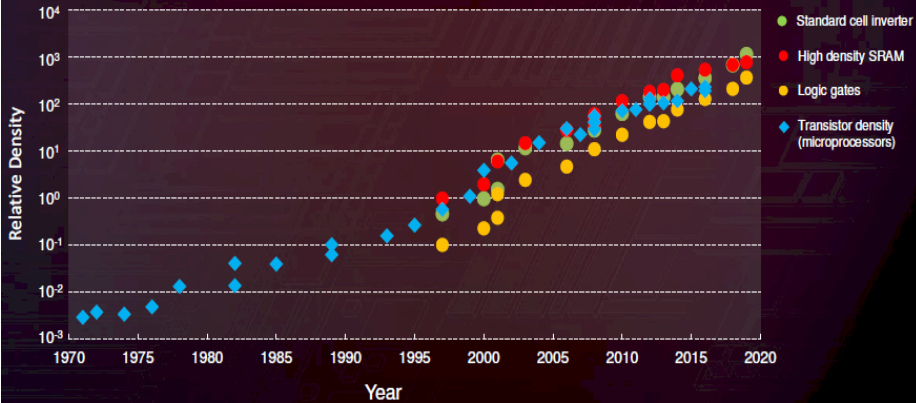
Microelectronics Growth

Traditionally based on Moore's law

Technology scales 2x every 18 months – sustained by transistor scaling

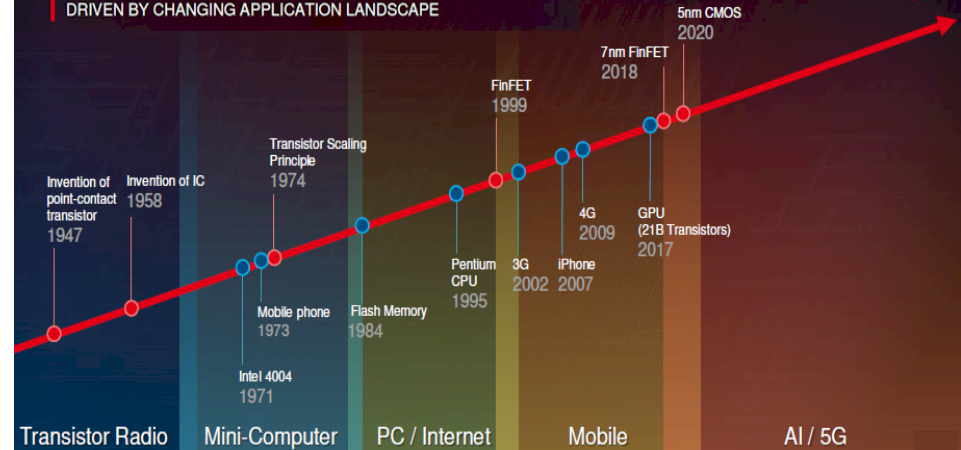
MOORE'S LAW IS WELL AND ALIVE

DENSITY: A NECESSARY ATTRIBUTE



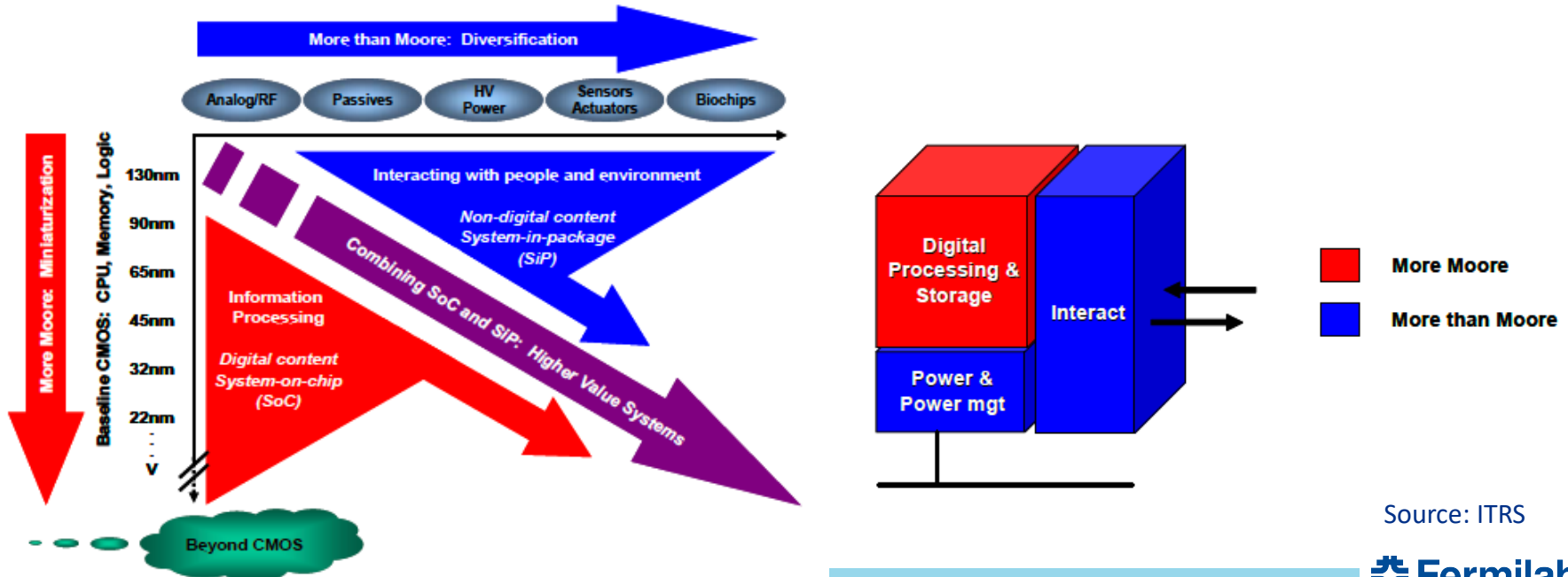
SEMICONDUCTOR TECHNOLOGY EVOLVES

DRIVEN BY CHANGING APPLICATION LANDSCAPE



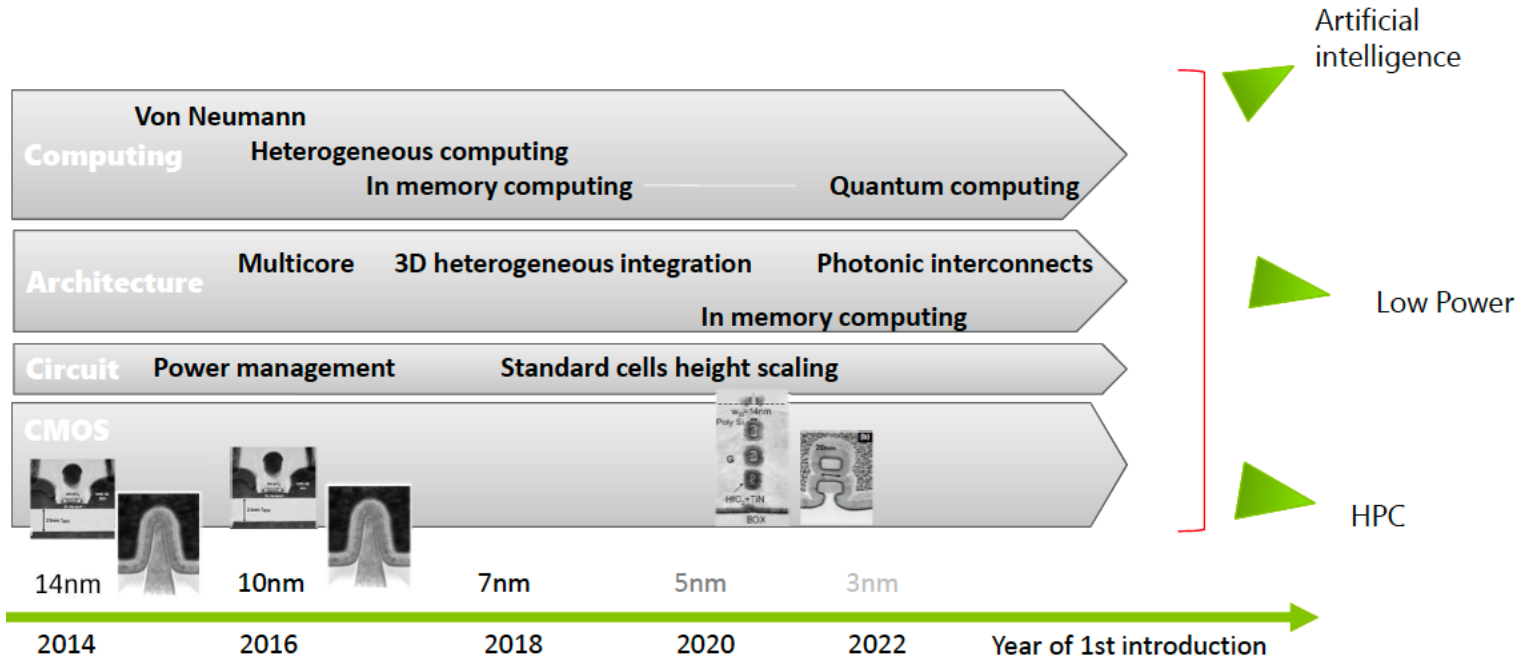
More than Moore?

- World is inherently analog (mandates an analog interface)
- System requires various functions (beyond just digital)
- Multi technology platforms



Source: ITRS

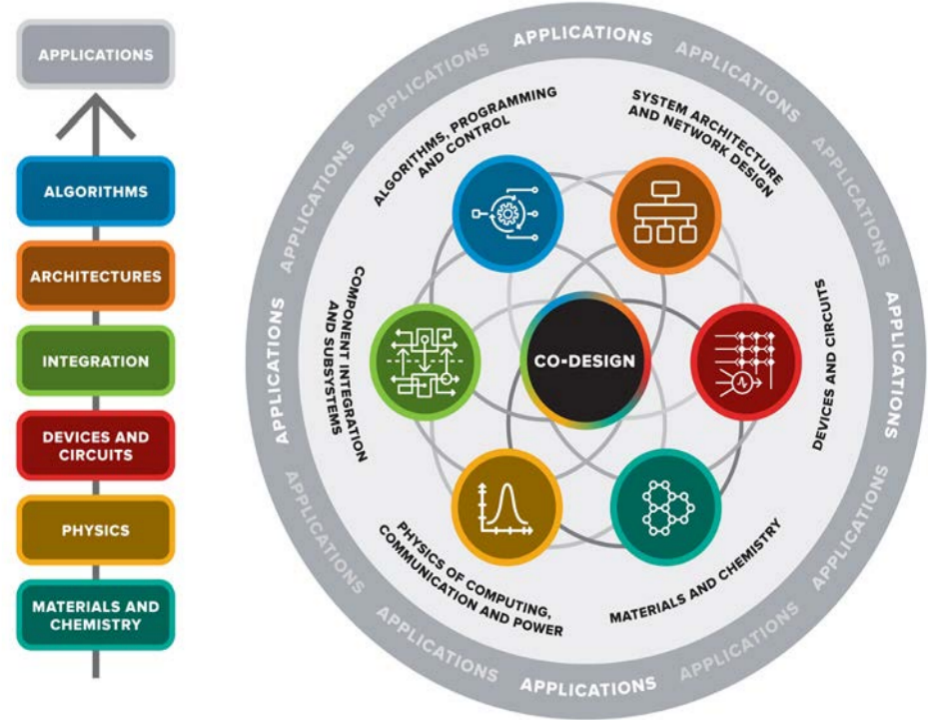
Why do we need more than Moore



Source: CEA- LETI

Microelectronics enabling next generation HEP instrumentation

- **Novel devices**
 - Skipper CCD-in-CMOS
- **Deep Cryogenic electronics**
 - Quantum Communication & Computing
- **Hybrid integration**
 - Electronic – Photonic Integration
 - 3D integration
- **Hardware – Software codesign to enable edge compute**
 - On-chip machine learning

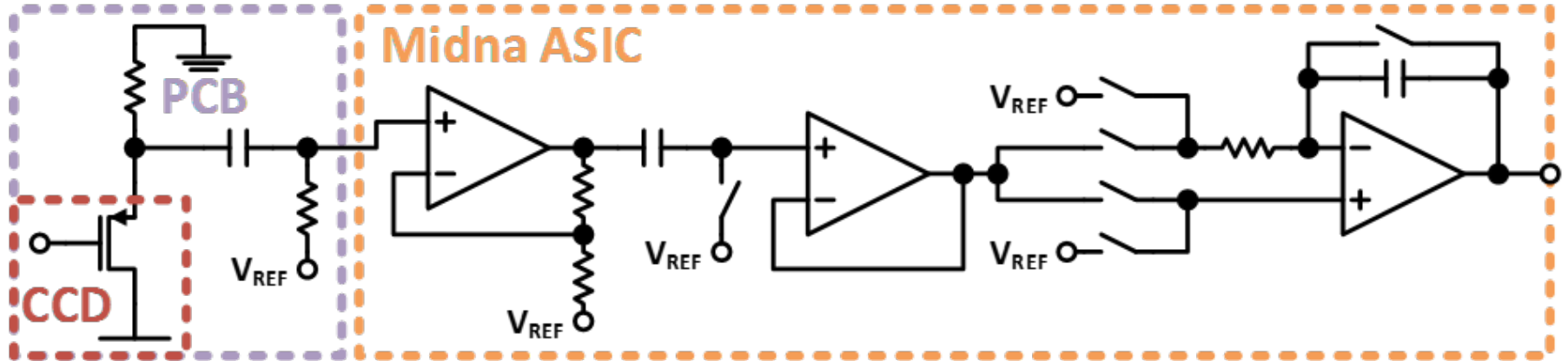


Novel Devices

Future CCD technologies

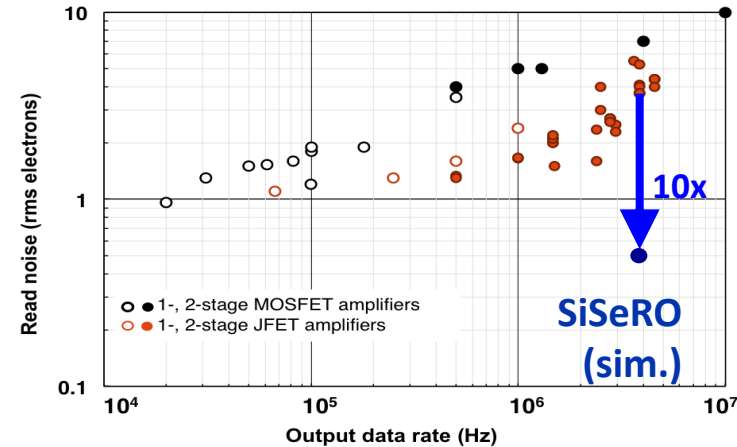
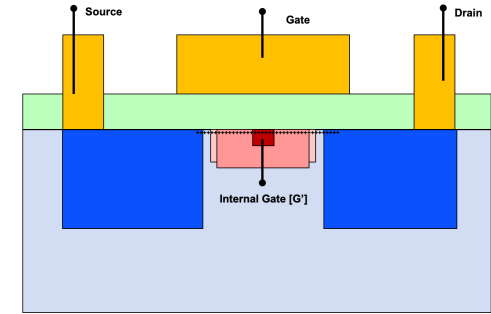
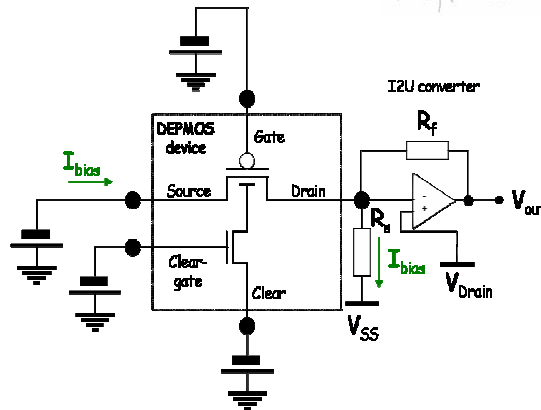
- Fermilab has been pioneering Skipper CCD technologies – Averaging multiple samples for ultra-low noise performance (~ 1000 averages for $\ll 1e-$ noise) – Juan Estrada
- 1st Step – Enable parallel readout with low-cost multiple channels. Translate PCB design to Readout Integrated Circuit (ROIC) with lower noise performance (1/3rd CCD noise) and $\sim 8\text{mW}$ power per channel.
- 4" \times 4" board to $\sim 4 \times 4 \text{ mm}^2$
- Cost reduction of 100 \times

T. England, F. Alcalde Bessia, H. Sun, L. Stefana (SCD)



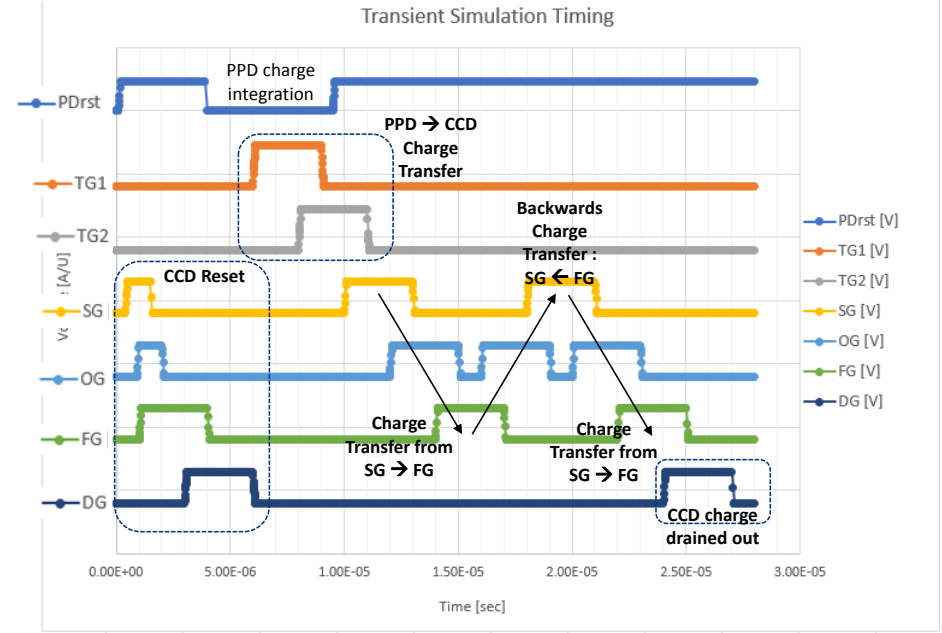
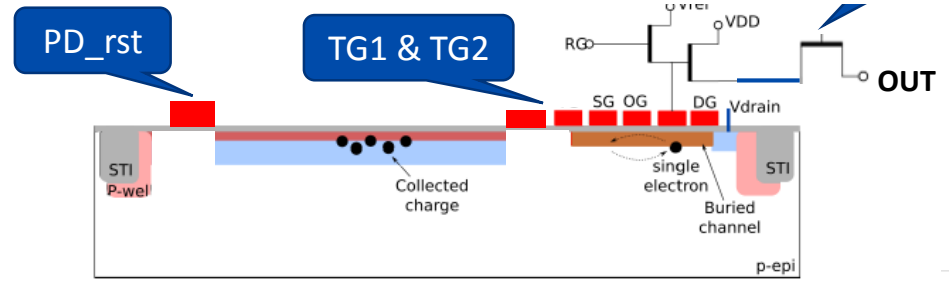
Future CCD technologies

- 2nd Method – Increase readout speed without increasing noise. SiSeRO approach (Collaboration with MIT Lincoln Lab)
- 10 × speed improvement
- Additional advantages – readout is DC coupled at low operating voltages (removes AC coupling capacitors and further increases system integration and reduces footprint)



Future CCD technologies

- Ultimate approach – skipper-in-CMOS
- Utilize a commercial CMOS Image Sensor process for lower noise performance (Collaboration with SLAC and Tower Semiconductor)
- Noise of a pinned photodiode ($0.7e^-$)
- With 10 averages we hope to achieve $\sim 0.2e^-$ noise
- Allows hybrid pixel sensor with fully-parallel (per pixel) readout achieving the ultimate goal of 1kfps readout over large areas (6 cm^2) ~ 2.5 Mpixels per chip



Deep Cryoelectronics for Quantum Computing

Quantum communication: Superconducting Nanowire Single Photon detectors

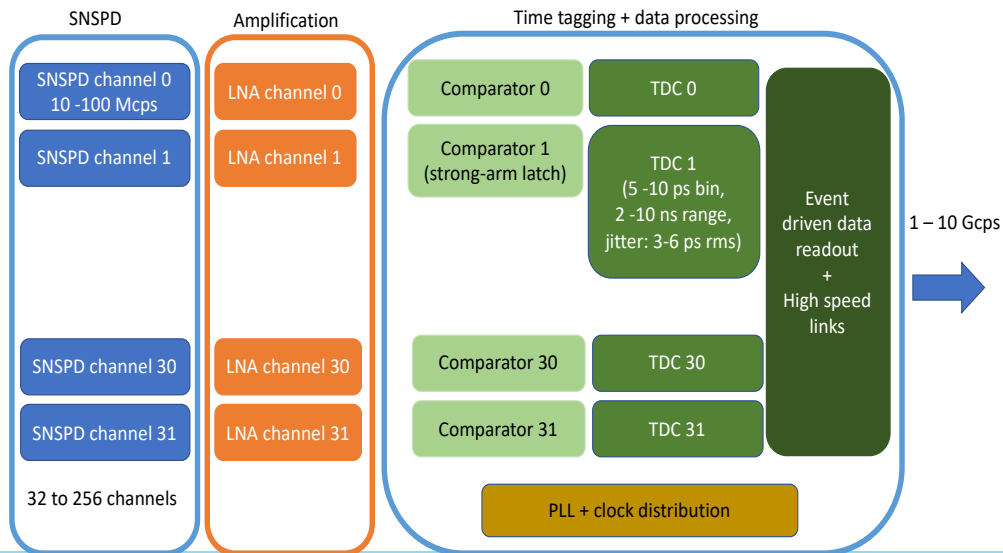
SNSPD best performance – (operating at 1 - 4K)

Time-correlated single photon counting from the deep UV to the mid-infrared

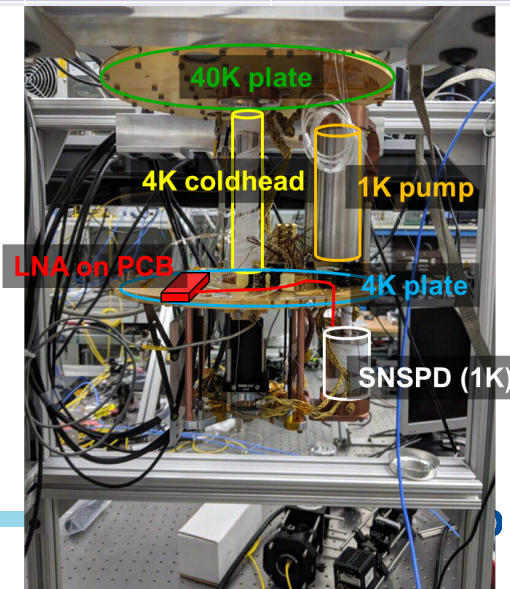
Extremely low dark counts and very high precision

QUANTUM INTERNET - High bandwidth communication

1st Step – Low Noise amplification in collaboration with Georgia Tech and JPL



Parameter	Goal by 2025	SOA 2019
Efficiency	>80% @ 10 μm	98% @ 1550 nm
Dark Counts	< 1e-6 cps / mm ²	< 1e-4 cps / mm ²
Energy Threshold	12.5 meV (100 μm)	0.125 eV (10 μm)
Timing Jitter	< 1 ps	2.7 ps
Active Area	100 cm ²	0.92 mm ²
Max Count Rate	100 Gcps	1.2 Gcps
Pixel Count	1.6e7 (4096x4096)	1024 (32x32)

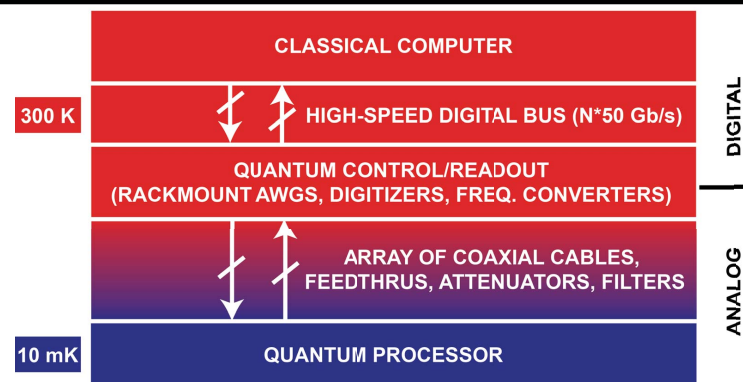


D. Braga

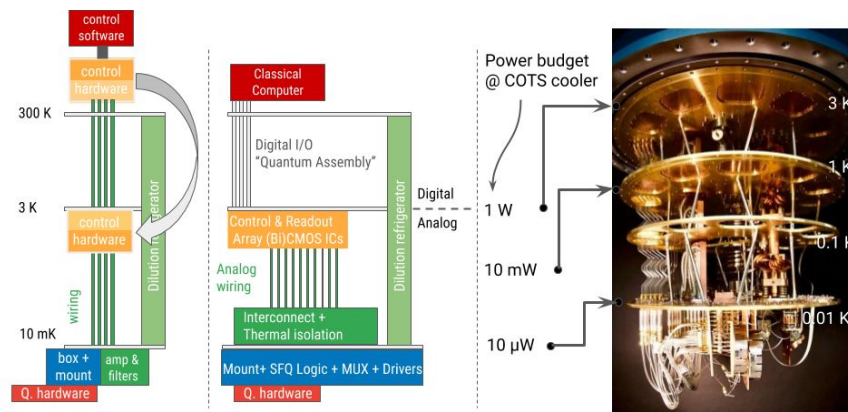
Beyond NISC era QC utilizing cryo-electronics

- Collaboration with industry (Microsoft – High speed ADC)
- Achieving high-speed and high-resolution are often conflicting goals
- Key transistor behavior – such as low noise performance improves at cryogenic temperature
- Why National Lab? [Cryogenic electronics for DUNE – full cycle from modelling to testing; very similar approach for radiation environment]
- Modelling is key (Collaboration with EPFL/ TUDELFT)

Architecture Suitable for 72 Qubit Computer



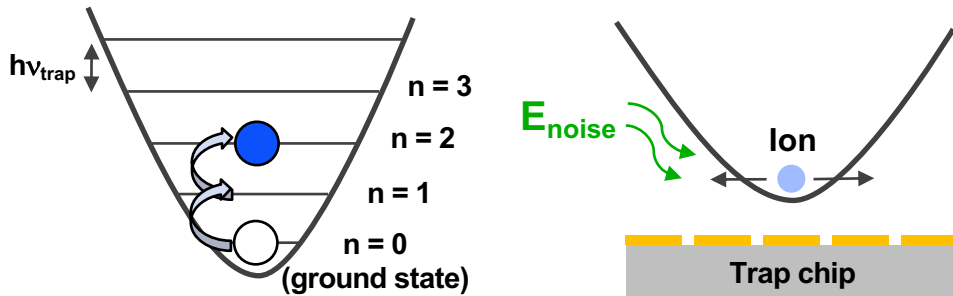
Scale by Integrating Control Electronics



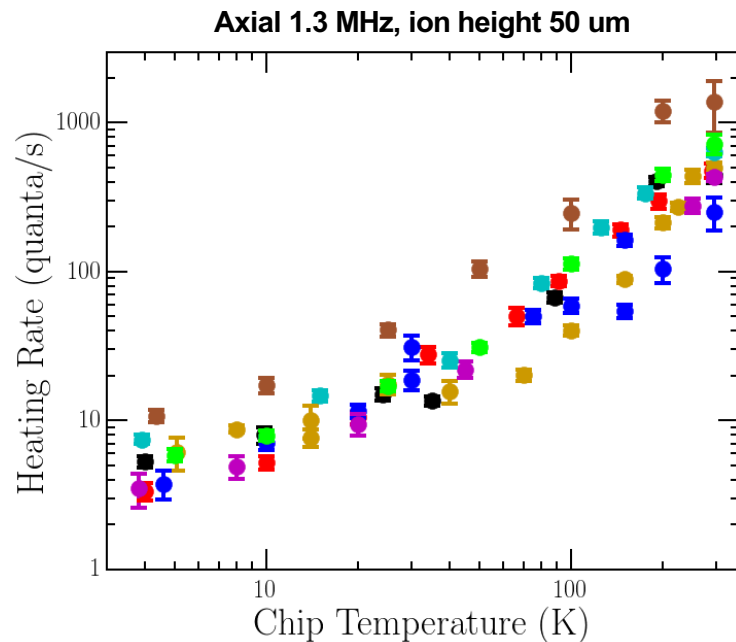


Benefits of Cryogenics for Trapped-Ion QIP

J.Chiaverini,
MIT LL



- **Greatly reduced electric-field noise**
 - This noise is a limiting factor in error in trapped-ion 2QGs in small traps
 - Measured to be much larger than JN (“anomalous”)
 - Source unknown
 - Empirically, 2 orders of magnitude lower at ~5K when compared to room temp.
 - This is true when technical noise is under control

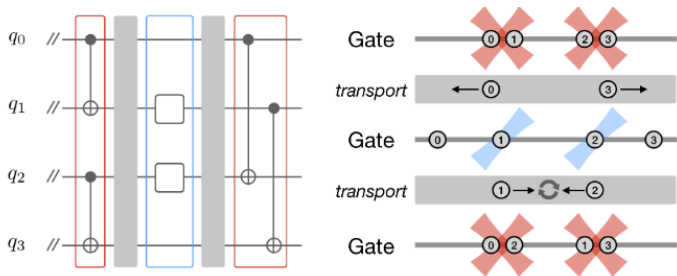


MIT-LL measurements

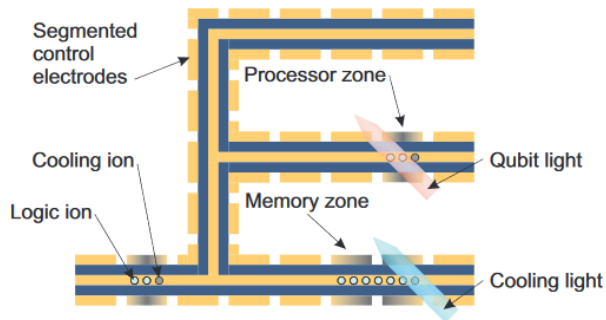


Motivation for Integrated Electronics

J.Chiaverini,
MIT LL



Pino et al., arXiv:2003.01293 (2020) [HQs]



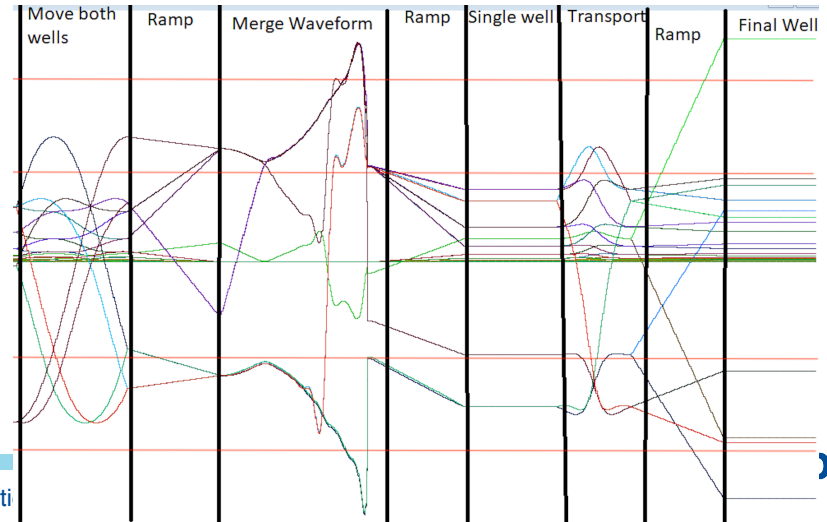
JC et al., Quant Inf. Comp. 5, 419 (2005) [NIST]

- **Controlled ion motion through variation of electrode potentials**
 - Each electrode segment requires a dedicated voltage for ion array control
 - For large arrays, electrical interconnects will become a limit
- **Multiplexing can reduce wiring overhead, but at a cost of speed**
- **On chip analog voltage production can directly address this issue**
 - Further level of on-chip control: microprocessor to implement time-dependent voltage updates
 - Standard motion subroutines, calibration, etc.

Cryo-electronics control for Ion-Traps (QSC - ORNL)

- **Design challenges:**

- Low output noise: $< 100\text{nV}/\sqrt{\text{Hz}}$ around a wide frequency range (0.5 - 5 MHz) and at low frequency.
- Low power: $< 5\text{ mW}/\text{DAC}$ (limited by the cooling power of the cryostat) while driving a wide range of load capacitance (70 – 1800 pF) of $\pm 10\text{ V}$ full scale at 10 MHz waveform updating rate.
- High resolution: 14-16 bit for precise control and not disturbing RF electrodes.
- Memory: 100 electrodes * 14 bit * 5000 points $\sim 2.5\text{ MB}$



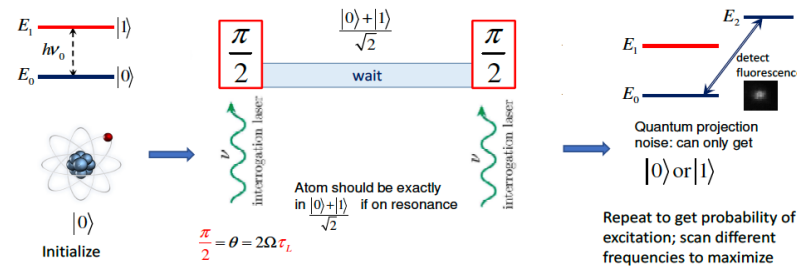
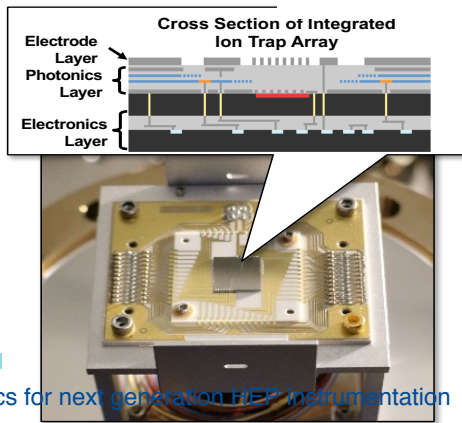
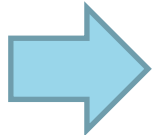
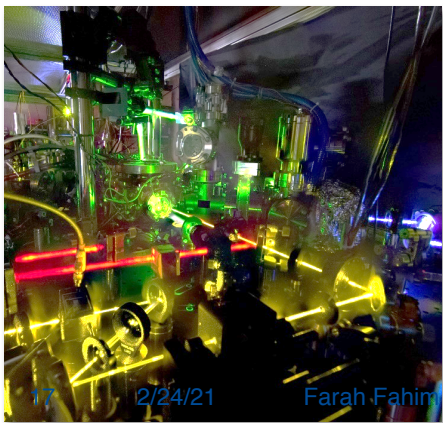
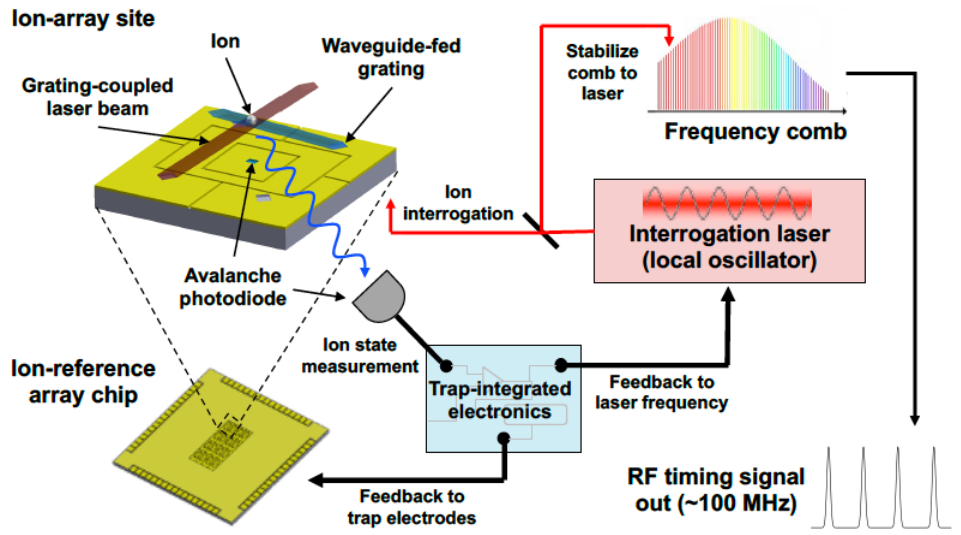
Hybrid Integration

Atomic Clock: Joint DOD – DOE project

Portable optical atomic clock with frequency instability of 10^{-16} over 10,000 sec

DOD – Atomic Photonic Integration
DOE – Electronic Photonic Integration

Create a closed loop compact system



Hardware-Software codesign: AI

Why do we need data processing on the edge

POWER: $CV^2f \times$ (data volume) problem

- Total power consumption to move data from pixel to periphery: 1 pJ/bit (\sim 5mm distance)
- Total power consumption to move data off-chip: > 0.1 nJ/bit

Minimize C,V

- 3D Integration (high density, low capacitance interconnect)
- Low voltage signaling

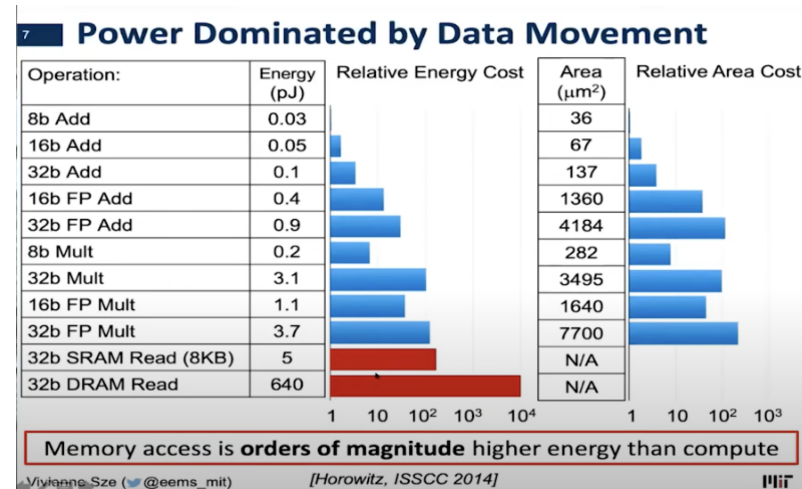
Reduce data

- Typically just zero-suppression for on-detector sparse data

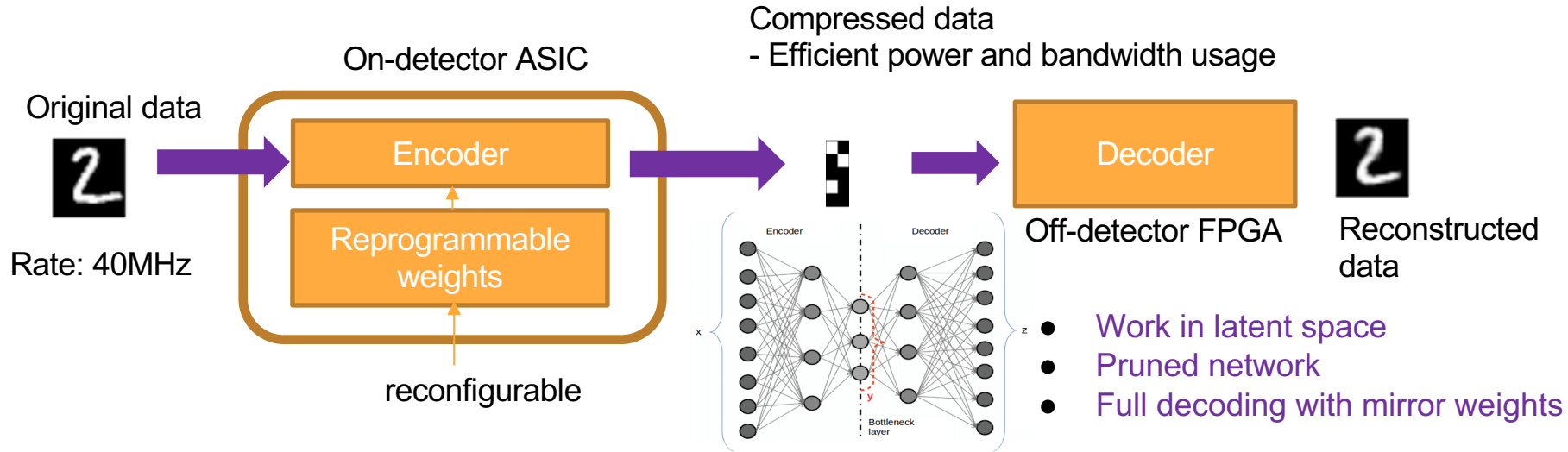
HL LHC:

Higher granularity, higher occupancy, higher precision

=> needs NEW APPROACH



Deep Neural Network: Autoencoder for data-compression

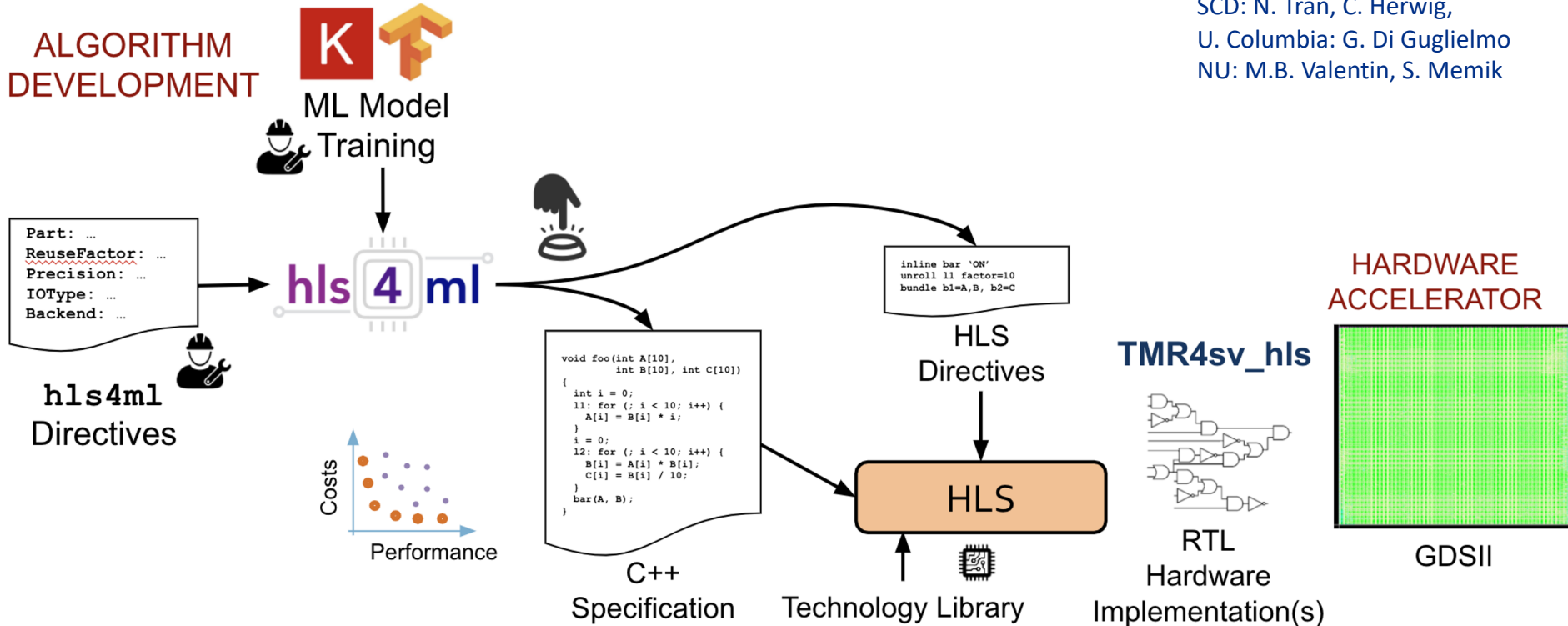


- Enable edge compute : Data compression for efficient usage of power and bandwidth
- Programmable and Reconfigurable: ability to reprogram weights to adjust for detector conditions and eventually lead to self-learning intelligent detectors
- Hardware – Software codesign : Algorithm driven architectural approach
- Optimized : Low power and Low latency
- Operating in extreme radiation environment: 200 M rad
- Autoencoder for data compression is the first use case towards a DNN based on-chip learning and inference²¹

Tool-kit development and Operation in rad-hard environment

- Integration of HLS generated and expert RTL
- Design code agnostic approach for implementation of various triplication methods

SCD: N. Tran, C. Herwig,
U. Columbia: G. Di Guglielmo
NU: M.B. Valentin, S. Memik



HL LHC High Granularity Calorimeter*: Data flow

CNN: Encodes information by correlating spatial features

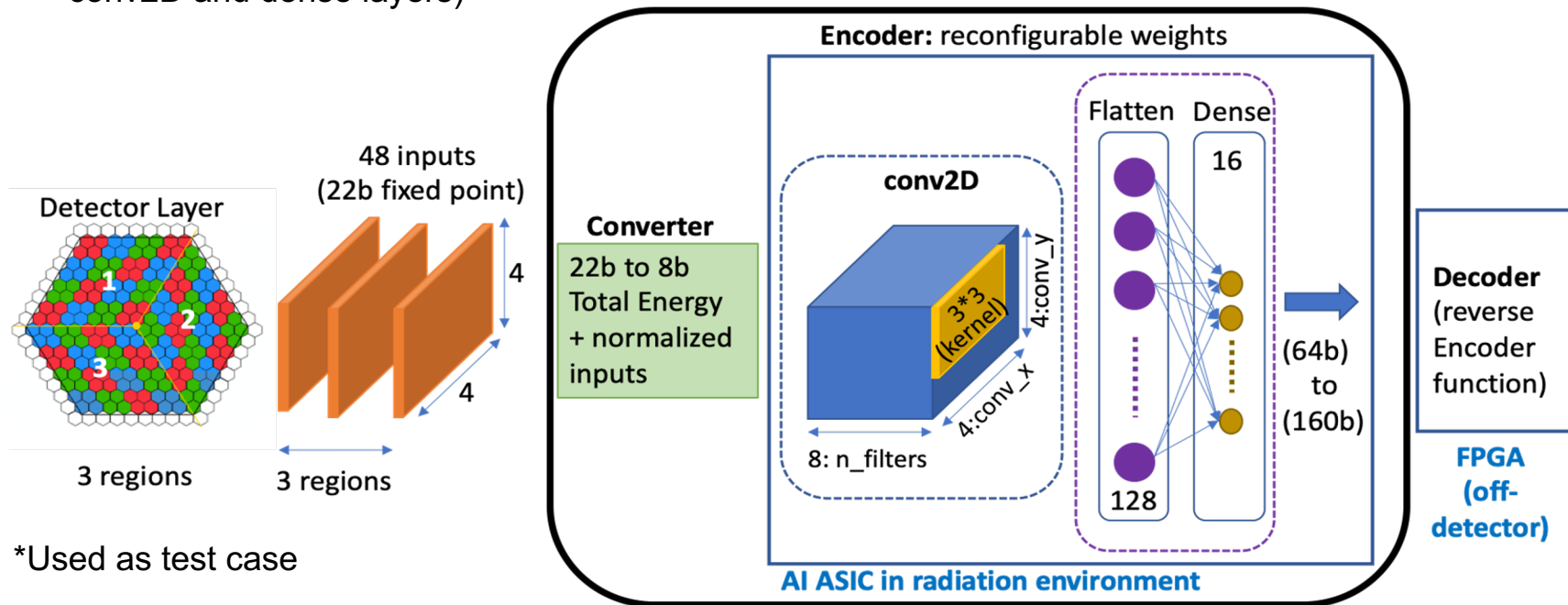
- **conv2D layer** – extract spatially correlated geometric features
- **Flatten layer** – Vectorizes the 2D image from the conv2D layer [8 x 4 x 4 = 128 x 1]
- **Dense layer** – aggregates the various features to provide higher order information
- **ReLU** – an activation function which introduces non-linearity by applying thresholds (part of both the conv2D and dense layers)

J. Hirschauer

SCD: N. Tran, C. Herwig,

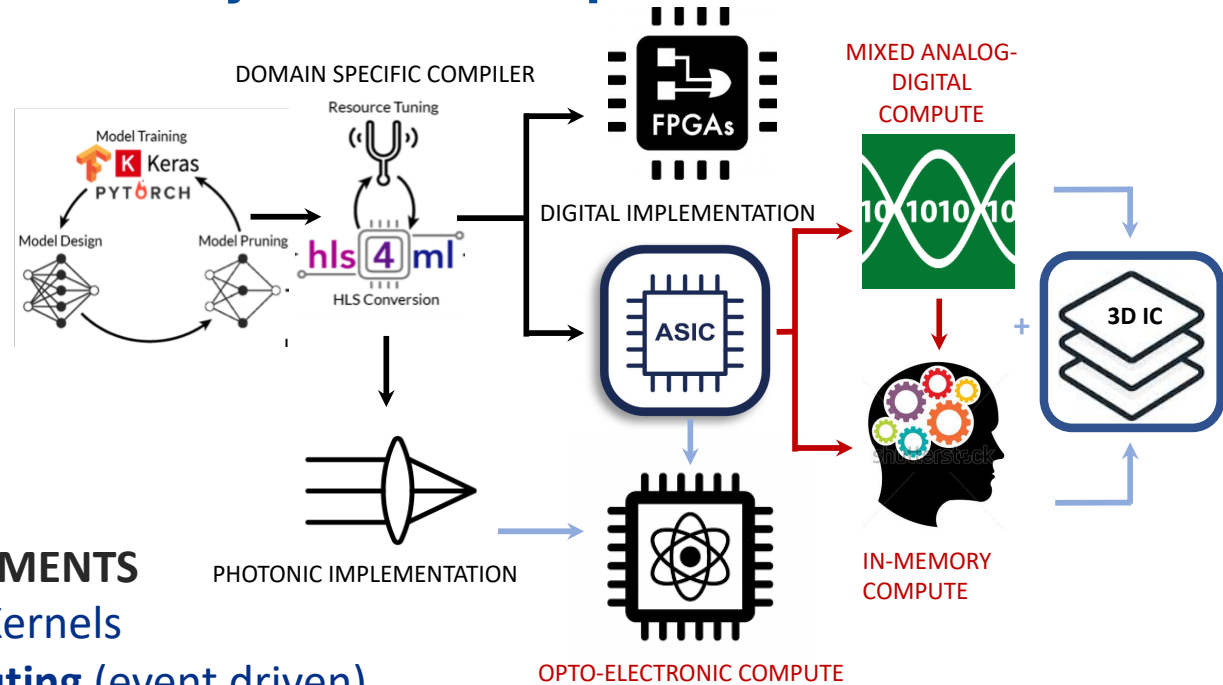
U. Columbia: G. Di Guglielmo

NU: M.B. Valentin, S. Memik



*Used as test case

Towards heterogenous system on-chip

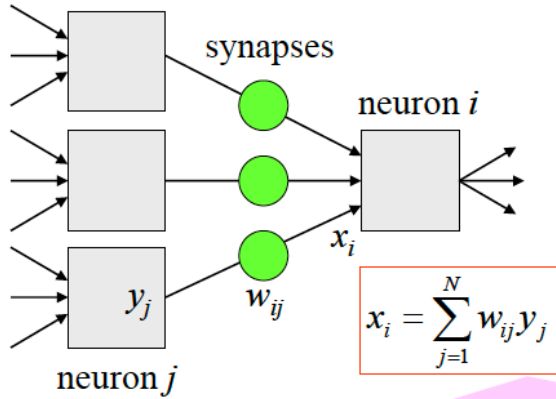


OPTIMIZATION REQUIREMENTS

- Analog Mixed-Signal Kernels
- **Neuromorphic computing** (event driven)
- In-memory compute (**non-Von Neumann approaches**) – new materials
- **Electronic-Photonic conversion**
- **Hybrid integration**

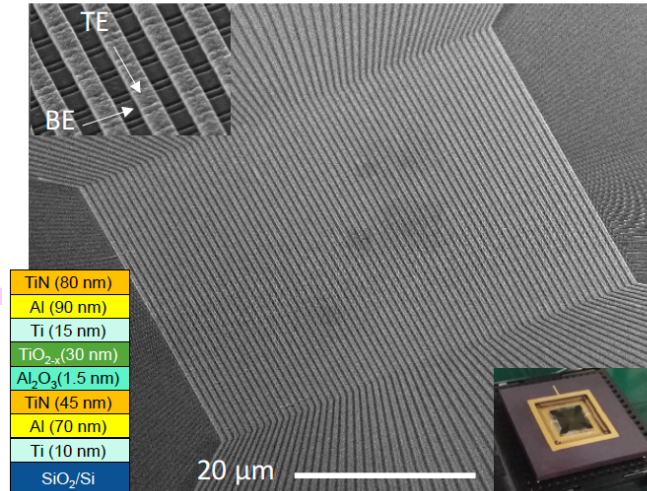
Vector Matrix Multiplication for Neural Networks

Vector-by-Matrix Multiplication ...



UC Santa Barbara's Metal-Oxide Memristors

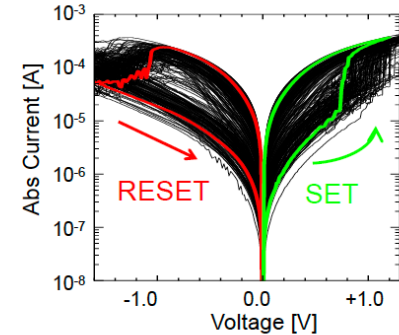
- 64 × 64 passive crossbar circuit



H. Kim et al. arXiv 2019

Background work: M. Prezioso et al., Nature 521, 61 2015, M. Prezioso et al. IEDM'15 p. 17.4.1, 2015, F. Merrikh Bayat et al. Nature Comm., 2018

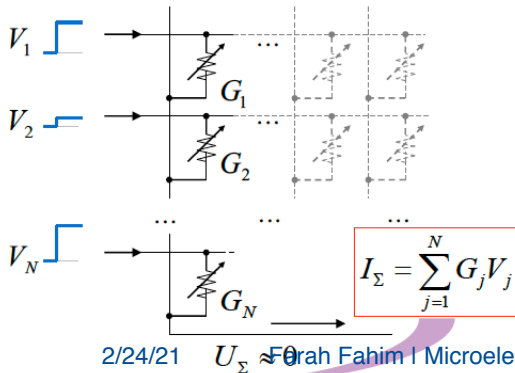
- Typical I-V characteristics



Details:

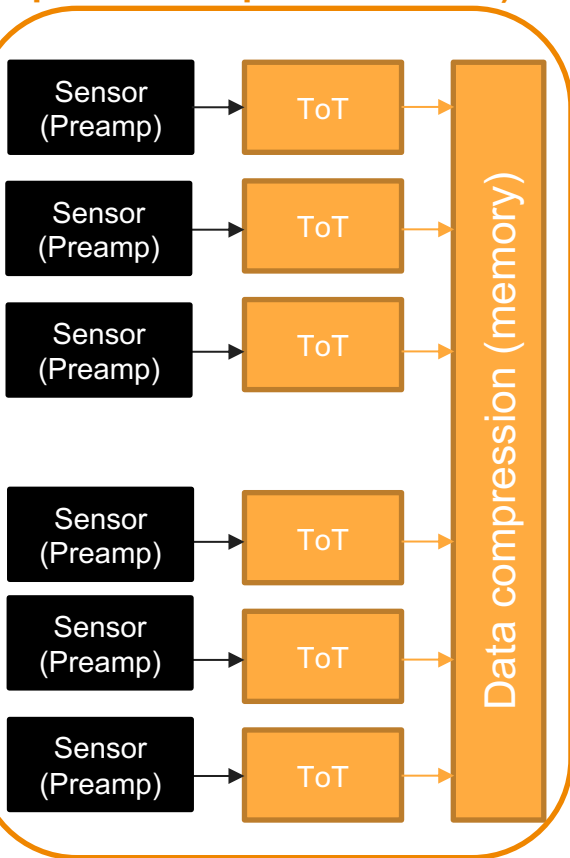
- Al₂O₃/TiO_{2-x} active bilayer by reactive sputtering
- CMOS-compatible CMP/dry etching process and TiN/Al electrodes for higher conductance
- ~250 nm wide lines
- The largest functional analog-grade passive memristor crossbar circuit supported by proper statistics

... by Analog Circuit

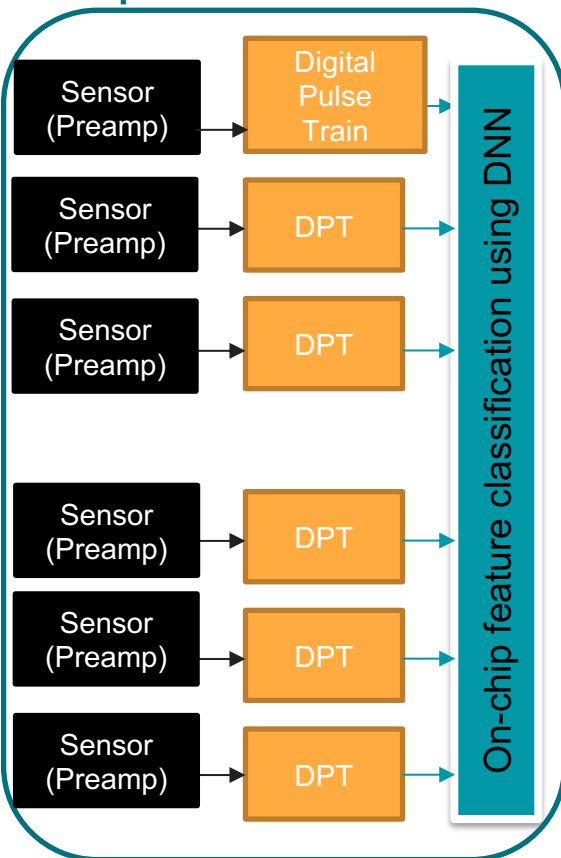


In-Pixel AI

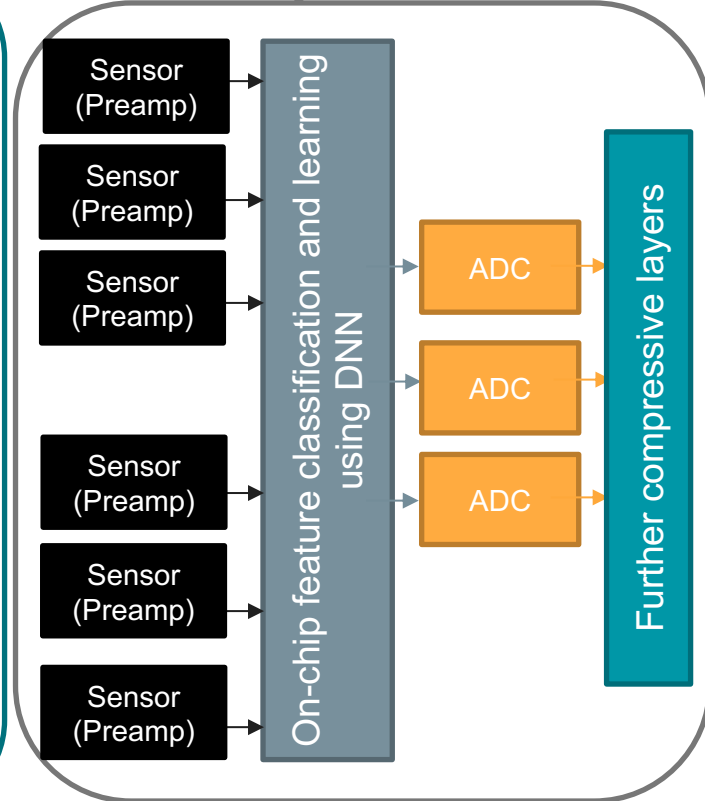
Current (digitization and high speed off-chip data transfer)



Digital neuromorphic implementation



Analog – Mixed Signal implementation using floating gates or memristive cross-bar arrays



Thankyou